



AP2331TD

0.2A SINGLE CHANNEL CURRENT-LIMITED LOAD SWITCH WITH OUTPUT TRANSIENT DISCHARGE

(Top View)

3 IN

Description

The AP2331TD is a single channel current-limited integrated high-side power switcher optimized for hot-swap applications. The devices have fast short-circuit response time for improved overall system robustness and provide a complete protection solution for application subject to heavy capacitive loads and the prospect of short circuit. It offers reverse-current blocking, over-current, over-temperature and shortcircuit protection, as well as controlled rise time and under-voltage lockout functionality.

The device is available in SOT23 and SC59 packages.

Features

- Quick Turn-off of Output Discharge Path at Power Down
- Input Voltage Range: 2.7V to 5.2V
- Fast Short-Circuit Response Time
- 0.4A Accurate Current Limiting
- 250mΩ On-Resistance
- Reverse-Current Blocking
- Built-In Soft-Start with 0.7ms Typical Turn-On Time
- Over-Current Protection
- Over-Voltage Protection
- Short-Circuit and Thermal Protection
- ESD Protection: 3kV HBM, 300V MM
- Ambient Temperature Range: -40°C to +85°C
- Available in "Green" Molding Compound (No Br, Sb)
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- UL Recognized, File Number E322375
- IEC60950-1 CB Scheme Certified

GND 1

Pin Assignments

(Top View) GND 1 3 IN

SC59

SOT23

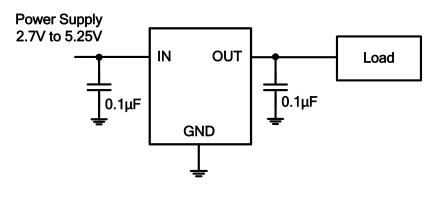
Applications

- LCD TVs & Monitors
- Set-Top Boxes, Residential Gateways
- Laptops, Desktops, Servers
- Printers, Docking Stations, HUBs
- Smart Phones, e-Readers

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Typical Application Circuit





Pin Descriptions

Pin Name	Pin Number	Functions
GND	1	GND
OUT	2	Switch Output Pin
IN	3	Voltage Input Pin

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Ratings	Unit
ESD HBM	Human Body Model ESD Protection	3	kV
ESD MM	Machine Model ESD Protection	300	V
V _{IN}	Input Voltage Relative to GND	6.5	V
Vout	Output Voltage Relative to GND	V _{IN} +0.3	V
I _{LOAD}	Maximum Continuous Load Current	Internal Limited	А
T _{JMAX}	Maximum Junction Temperature	+150	°C
T _{ST}	Storage Temperature Range (Note 4)	-65 to +150	°C

Note: 4. UL Recognized Rating from -30°C to +70°C (Diodes Incorporated qualified T_{ST} from -65°C to +150°C).

Recommended Operating Conditions (@T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Min	Мах	Unit
V _{IN}	Input Voltage Relative to GND	2.7	5.2	V
IOUT	Output Current	0	0.2	А
T _A	Operating Ambient Temperature	-40	+85	°C

Electrical Characteristics (@T_A = +25°C, V_{IN} = 5V, unless otherwise specified.)

Symbol	Parameter	Test Conditions (Note 5)	Min	Тур	Max	Unit
VUVLO	Input UVLO	V _{IN} rising	2.35	—	2.65	V
lq	Input Quiescent Current	Above UVLO, I _{OUT} = 0	_	85	125	μA
I _{REV}	Reverse Leakage Current	$V_{IN} = 0V, V_{OUT} = 5V, I_{REV} \text{ at } V_{IN}$	_	0.01	0.10	μA
R _{DS(ON)}	Switch On-resistance	V _{IN} = 5V, I _{OUT} = 0.2A	100	250	350	mΩ
ILIMIT	Over-load Current Limit	$V_{IN} = 5V, V_{OUT} = 4V$	0.3	0.4	0.5	A
I _{OS}	Short-circuit Current	OUT shorted to ground	0.3	0.4	0.5	Α
I _{ROCP}	Reverse-current Trigger Point	$V_{IN} = 5.0V, V_{OUT} = 5.2V$	_	0.20	0.25	A
t _{TRIG}	Deglitch Time from Reverse Current Trigger to MOSFET Turn Off	(Note 6)	0.5	0.7	1.0	ms
V _{OVP}	Output Over-voltage Trip Point	(Note 7)	5.3	—	5.6	V
t _{OVP}	Debounce Time from Output Over-voltage to MOSFET Turn Off	_	—	15	_	μs
V _{REC}	Recovery after Turn-off from ROCP and OVP	_	_	101%*V _{IN}	_	V
t _{ON}	Output Turn-on Time (Note 8)	$C_L = 0.1 \mu F$, $R_{LOAD} = 20\Omega$ (UVLO to 90% V _{OUT-NOM})	_	0.7	_	ms
T _{SHDN}	Thermal Shutdown Threshold	V _{IN} = 2.7V to 5.25V	_	+150	_	°C
T _{HYS}	Thermal Shutdown Hysteresis		_	+20	_	°C
	Thermal Resistance Junction-to-Ambient	SOT23	_	215	_	°C/W
θја	(Note 9)	SC59	_	255		°C/W

5. Pulse-testing techniques maintain junction temperature close to ambient temperature; thermal effects must be taken into account separately.

6. When reverse current triggers at I_{ROCP} = 0.20A, the reverse current is continuously clamped at I_{ROCP} for 0.7ms deglitch time until MOSFET is turned off.

7. During output over-voltage protection, the output draws approximately $60\mu\text{A}$ current.

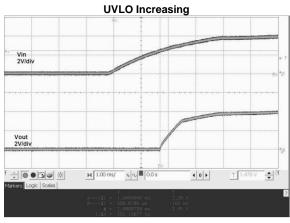
9. Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.

Notes:

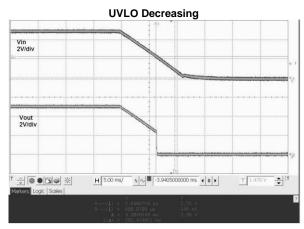
^{8.} Since the output turn-on slew rate is dependent on input supply slew rate, this limit is only applicable for input supply slew rate between $V_{IN}/0.2ms$ to $V_{IN}/1ms$.



Typical Performance Characteristics

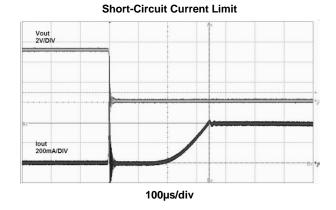


1ms/div

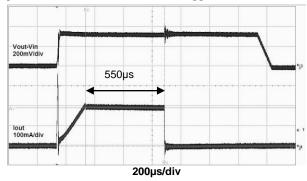


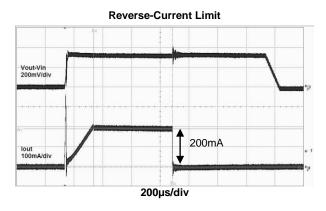
5ms/div

Over-Load Current Limit



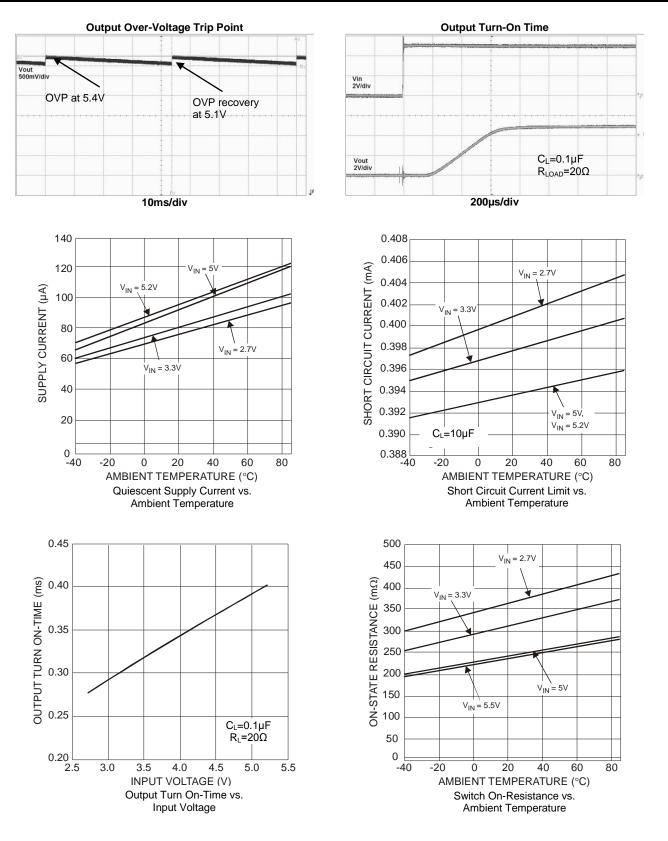
Deglitch Time from Reverse-Current Trigger to MOSFET Turn-Off





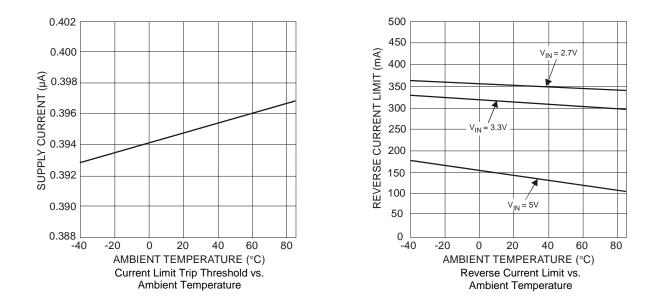


Typical Performance Characteristics (Cont.)





Typical Performance Characteristics (Cont.)





Application Information

Input and Output Capacitors

Minimum 0.1µF ceramic bypass capacitor from VIN to GND, located near the device, is strongly recommended to suppress the ringing during short circuit condition. 0.1µF close to device output pin is also required to reduce output transient voltage on a short event.

Under-Voltage Lockout (UVLO)

Under-voltage lockout function (UVLO) guarantees that the internal power switch is initially off during start-up. The UVLO functions only when the power supply has reached at least 2.5V (TYP). Whenever the input voltage falls below approximately 2.5V, the power switch is turned off. This facilitates the design of hot-insertion systems where it is not possible to turn off the power switch before input power is removed.

Over-Current and Short-Circuit Protection

An internal sensing FET is employed to check for over current conditions. Unlike current-sense resistors, sense FETs do not increase the series resistance of the current path. When an over current condition is detected, the device maintains a constant output current and reduces the output voltage accordingly. Complete shutdown occurs only if the fault stays long enough to activate thermal limiting.

The different overload conditions and the corresponding response of the AP2331TD are outlined below:

S.NO.	Conditions	Explanation	Behavior of the AP2331TD
1	Short-circuit condition at start-up	Output is shorted before input voltage is	The IC senses the short circuit and immediately clamps
	Short-circuit condition at start-up	applied or before the part is powered up.	output current to a certain safe level namely ILIMIT
2	Short-circuit or Over current condition	Short-Circuit or Overload condition that occurs when the part is powered up and above UVLO.	At the instance the overload occurs, higher current may flow for a very short period of time before the current limit function can react. After the current limit function has tripped (reached the over-current trip threshold), the device switches into current limiting mode and the current is clamped at I_{LIMIT} .
3	Gradual increase from nominal operating current to I _{LIMIT}	Load increases gradually until the current-limit threshold.	The current rises until I_{LIMIT} . Once the threshold has been reached, the device switches into its current limiting mode and is clamped at I_{LIMIT} .

Reverse-Current Protection

The USB specification does not allow an output device to source current back into the USB port. In a normal MOSFET switch, current will flow in reverse direction (from the output side to the input side) when the output side voltage is higher than the input side. A reverse current limit feature is implemented in the AP2331TD to limit such back currents. Reverse current limit is always active in AP2331TD. Reverse current is limited at I_{ROCP} level and when the fault exists for more than 700µs, output device is disabled and shut down. This is called the "Deglitch time from reverse current trigger to MOSFET turn off." Recovery from I_{ROCP} occurs when the output voltage falls to 101% of input voltage.

Over-Voltage Protection

The device has an output over-voltage protection that triggers when the output voltage reaches 5.3V (MIN). When this fault condition stays on for longer than 15µs, (This is called the "Debounce time from output over voltage to MOSFET turn off") output device is disabled and shut down.

Recovery from ROVP occurs when the output voltage falls to 101% of input voltage.

Thermal Protection

Thermal protection prevents the IC from damage when the die temperature exceeds safe margins. This mainly occurs when heavy-overload or short-circuit faults are present for extended periods of time. The AP2331TD implements a thermal sensing to monitor the operating junction temperature of the power distribution switch. Once the die temperature rises to approximately +150°C, the Thermal protection feature gets activated as follows: The internal thermal sense circuitry turns the power switch off thus preventing the power switch from damage. Hysteresis in the thermal sense circuit allows the device to cool down to approximately +20°C before the output is turned back on. This built-in thermal hysteresis feature is an excellent feature, as it avoids undesirable oscillations of the thermal protection circuit. The switch continues to cycle in this manner until the load fault is removed, resulting in a pulsed output.

Discharge Function

When input voltage falls below UVLO, the discharge function is active. The output capacitor is discharged through an internal NMOS that has a discharge resistance of $1.8k\Omega$. Hence, the output voltage drops down. The internal discharge NMOS is turned off right away to avoid leakage current from output. The transient output discharge feature makes it suitable for HDMI applications.



Application Information (Cont.)

Power Dissipation and Junction Temperature

The low on-resistance of the internal MOSFET allows the small surface-mount packages to pass large current. Using the maximum operating ambient temperature (T_A) and R_{DS(ON)}, the power dissipation can be calculated by:

 $P_D = R_{DS(ON)} \times I^2$

Finally, calculate the junction temperature:

 $T_J = P_D \times R_{\theta JA} + T_A$

Where:

 T_A = Ambient Temperature °C $R_{\theta JA}$ = Thermal Resistance P_D = Total Power Dissipation

Layout Consideration

Good PCB layout is important for improving the thermal performance of the device. All trace lengths should be kept as short as possible. The input (IN) and output (OUT) PCB traces should be as wide as possible to reduce stray impedance. Use a ground plane to enhance the power dissipation capability of the device if applicable.

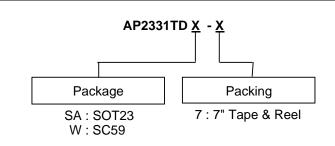
1. Please place the input capacitors near the IN pin as close as possible to minimize the effects of parasitic inductance.

2. Output decoupling capacitors must be placed near the device as close as possible for decoupling transient noises.

3. The negative pins of the input and output capacitors and the GND pin must be connected to the ground plane of the load.

4. Keep VIN and VOUT traces as wide and short as possible.

Ordering Information

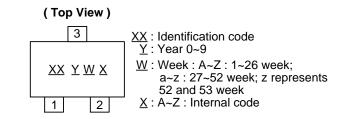


Part Number	Package Code	Packaging	7" Tape and Reel	
Fait Nulliper	Fackage Code	(Note 10)	Quantity	Part Number Suffix
AP2331TDSA-7	SA	SOT23	3000/Tape & Reel	-7
AP2331TDW-7	W	SC59	3000/Tape & Reel	-7

Note: 10. Pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found on our website at http://www.diodes.com/package-outlines.html.



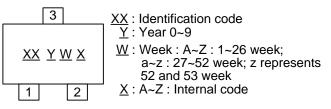
(1) SOT23



Part Number	Package	Identification Code
AP2331TDSA-7	SOT23	KP

(2) SC59





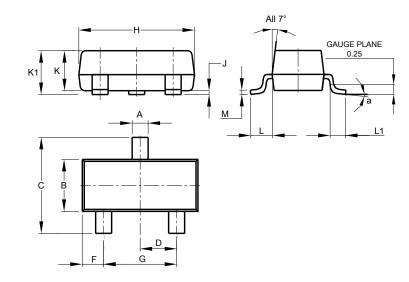
Part Number	Package	Identification Code
AP2331TDW-7	SC59	KR



Package Outline Dimensions

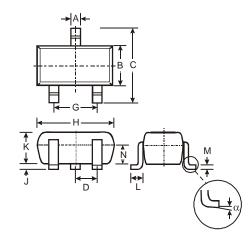
Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) SOT23



	SOT23				
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
К	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
Μ	0.085	0.150	0.110		
а	0°	8°			
All	Dimens	ions in	mm		

(2) SC59



	SC	59	
Dim	Min	Max	Тур
Α	0.35	0.50	0.38
В	1.50	1.70	1.60
С	2.70	3.00	2.80
D	-	-	0.95
G	-	-	1.90
Н	2.90	3.10	3.00
J	0.013	0.10	0.05
κ	1.00	1.30	1.10
L	0.35	0.55	0.40
Μ	0.10	0.20	0.15
N	0.70	0.80	0.75
	0°	8°	-
All D	Dimens	ions in	mm

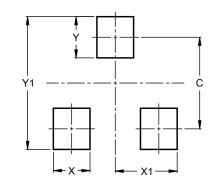
NEW PRODUCT



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

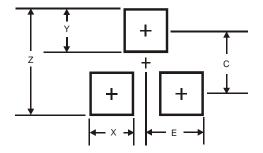
(1) SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9

(2) SC59

NEW PRODUCT



Dimensions	SC59
Z	3.4
Х	0.8
Y	1.0
С	2.4
E	1.35